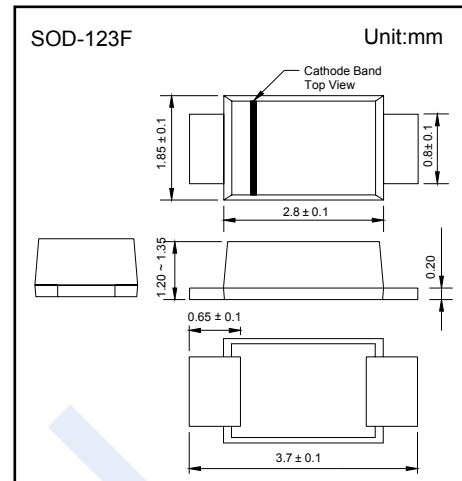


Schottky Diodes

SS1020F ~ SS10100F

■ Features

- Fast switching speed
- Low power loss, high efficiency
- Surface mount package ideally suited for automatic insertion



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	SS1020F	SS1030F	SS1040F	SS1060F	SS10100F	Unit
Repetitive Peak Reverse Voltage	VRRM						V
Reverse Breakdown Voltage @ IR=500μA	VBR	20	30	40	60	100	
Reverse Voltage	VR						
Forward Voltage Ta=65°C	VF	0.55			0.7	0.85	
Averaged Forward Current Ta=75°C	IFAV	1					A
Peak Forward Surge Current @ t=8.3ms	IFSM	30					
Reverse Voltage Leakage Current	IR	500					μA
Typical Junction Capacitance	Cj	60			50	40	pF
Junction Temperature	Tj	125					°C
Storage Temperature	Tstg	-55 to 125					

■ Marking

NO.	SS1020F	SS1030F	SS1040F	SS1060F	SS10100F
Marking	G2	G3	G4	G6	G10

Schottky Diodes SS1020F ~ SS10100F

■ Typical Characteristics

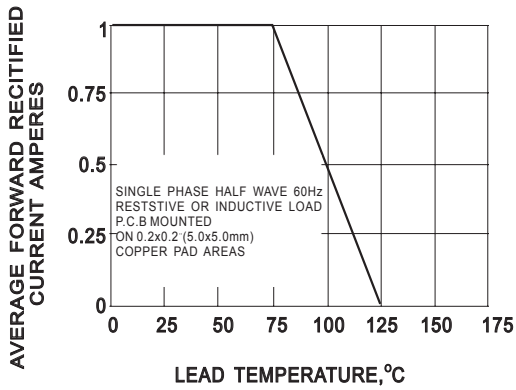


FIG. 1-FORWARD CURRENT DERATING CURVE

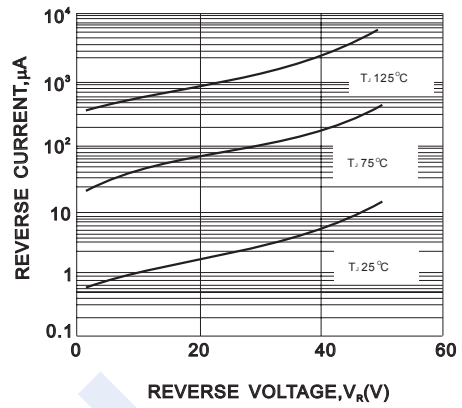


FIG. 2-TYPICAL REVERSE CHARACTERISTIC

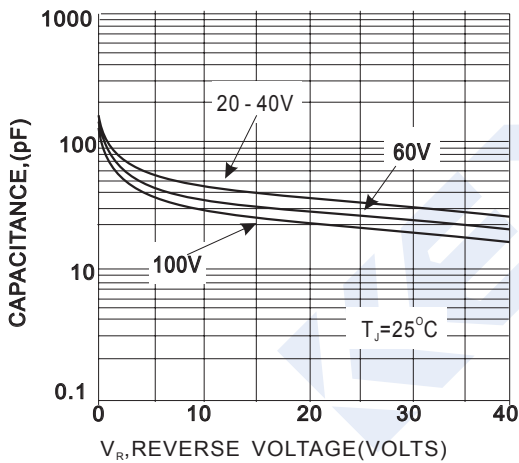


FIG. 3-TYPICAL JUNCTION CHARACTERISTIC

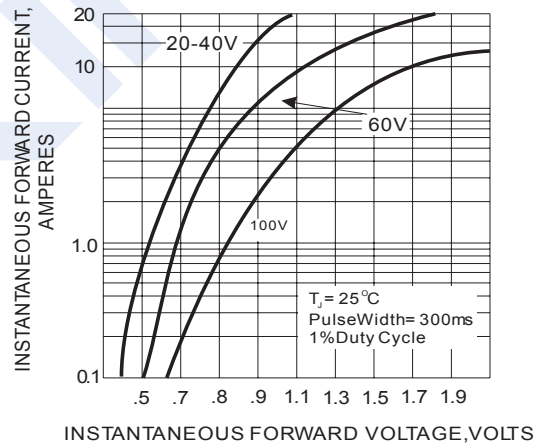


FIG. 4-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS